

Phase Control Thyristors (Hockey PUK Version), 650 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS						
I _{T(AV)}	650 A					
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V, 1400 V, 1600 V					
V _{TM}	1.90 V					
I _{GT}	100 mA					
T _J	-40 °C to +125 °C					
Package	B-PUK (TO-200AC)					
Circuit configuration	Single SCR					

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC))



- High profile hockey PUK
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		650	A				
I _{T(AV)}	T _{hs}	55	°C				
L		1230	А				
I _{T(RMS)}		25	°C				
1	50 Hz	9000	- A				
ITSM	60 Hz	9420	A				
² t	50 Hz	405	- kA ² s				
I-I	60 Hz	370	- KA-S				
V _{DRM} /V _{RRM}		400 to 1600	V				
tq	Typical	100	μs				
T _J		-40 to +125	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE F	VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA						
	04	400	500							
	08	800	900							
VS-ST330CL	12	1200	1300	50						
	14	1400	1500							
	16	1600	1700							

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PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS
Maximum average on-state current	L	180° condu	180° conduction, half sine wave		650 (314)	Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (75)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	1230	
		t = 10 ms	No voltage		9000	
Maximum peak, one-cycle	I _{TSM}	t = 8.3 ms	reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	9420	A kA ² s
non-repetitive surge current		t = 10 ms	100 % V _{RBM}		7570	
		t = 8.3 ms	reapplied		7920	
	l ² t	t = 10 ms	No voltage reapplied		405	
Maximum I ² t for fusing		t = 8.3 ms			370	
		t = 10 ms			287	
		t = 8.3 ms	reapplied		262	
Maximum I ² √t for fusing	I²√t	t = 0.1 to 10	ms, no voltage	reapplied	4050	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.91	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.57	11122
Maximum on-state voltage	V_{TM}	I _{pk} = 1730 A	$I_{pk} = 1730 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			V
Maximum holding current	I _H	T _ 05 °C	anada auppli: 1	2 V registive lead	600	mΛ
Typical latching current	ΙL	1 J = 25 °C,	anoue supply 1	2 V resistive load	1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	
Typical turn-off time	t _q	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/μs, V_R = 50 V, dV/dt = 20 V/μs, gate 0 V 100 Ω , t_p = 500 μs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA



TRIGGERING								
PARAMETER	SYMBOL	TEG	VALUES		UNITS			
PANAMETEN	STIMBOL	IES	TEST CONDITIONS					
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	10	0.0	W		
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV		
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	3	.0	Α		
Maximum peak positive gate voltage	+V _{GM}	T. – T. maximum	t < 5 ms	2	V			
Maximum peak negative gate voltage	-V _{GM}	ij = ij iliaxililulli,	$T_J = T_J$ maximum, $t_p \le 5$ ms					
		T _J = -40 °C		200	-			
DC gate current required to trigger	I _{GT}	T _J = 25 °C]	100	200	mA		
		T _J = 125 °C	Maximum required gate trigger/ current/voltage are the lowest		-			
		T _J = -40 °C	value which will trigger all units 12 V anode to cathode applied	2.5	-			
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 v anoue to camoue applied	1.8	3.0	V		
		T _J = 125 °C		1.1	-			
DC gate current not to trigger	I _{GD}	T T manyimay	Maximum gate current/voltage not to trigger is the maximum	10		mA		
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V		

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction temperature range	T_J		-40 to +125	°C			
Maximum storage temperature range	T _{Stg}		-40 to +150	C			
Maximum thermal resistance, junction to heatsink	D	DC operation single side cooled	0.11				
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation double side cooled	0.06	K/W			
Maximum thermal resistance, case to heatsink	В	DC operation single side cooled	0.011	IV VV			
Maximum thermal resistance, case to heatslink	R _{thC-hs}	DC operation double side cooled	0.005				
Mounting force, ± 10 %			9800 (1000)	N (kg)			
Approximate weight			250	g			
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	200AC)			

△R _{thJ-hs} CONDUCTION								
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR	R CONDUCTION	TEST CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS		
180°	0.012	0.010	0.008	0.008				
120°	0.014	0.015	0.014	0.014				
90°	0.018	0.018	0.019	0.019	$T_J = T_J$ maximum	K/W		
60°	0.026	0.027	0.027	0.028				
30°	0.045	0.046	0.046	0.046				

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

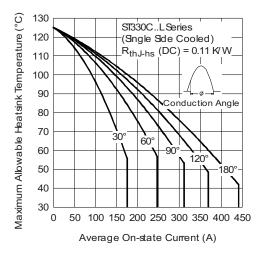


Fig. 1 - Current Ratings Characteristics

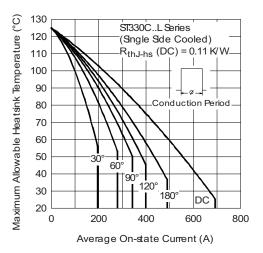


Fig. 2 - Current Ratings Characteristics

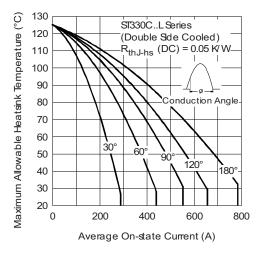


Fig. 3 - Current Ratings Characteristics

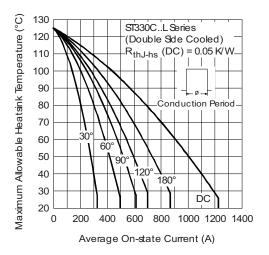


Fig. 4 - Current Ratings Characteristics

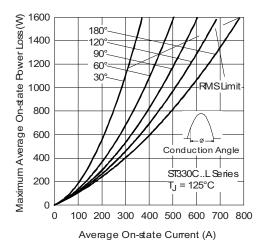


Fig. 5 - On-State Power Loss Characteristics

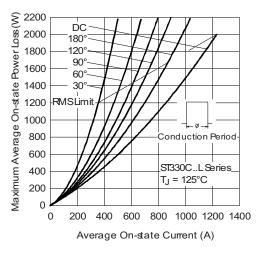


Fig. 6 - On-State Power Loss Characteristics

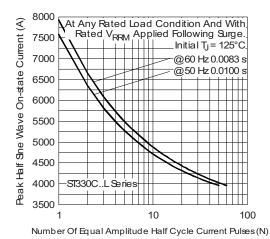


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

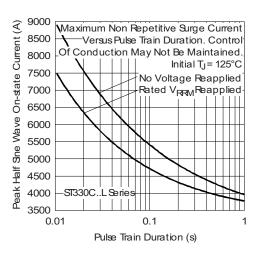


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

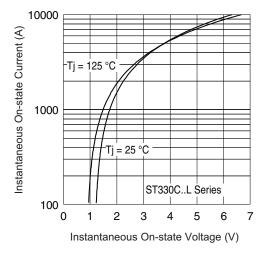


Fig. 9 - On-State Voltage Drop Characteristics

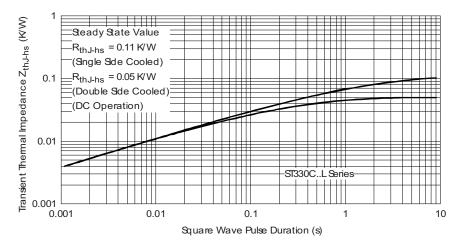


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

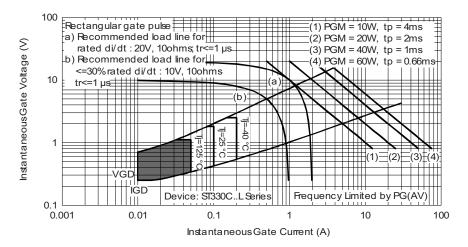


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	vs-	ST	33	0	С	16	L	1	-	
	1	2	3	4	5	6	7	8	9	
	1 -		-	niconduc	ctors pro	oduct				
	3 -	,	ristor ential pa	art numb	oer					
	4 -			er grade						
	5 -	C =	cerami	: PUK						
	6 -	Volt	age cod	de x 100	= V _{RRM}	(see V	oltage F	Ratings	table)	
	7 -	L =	PUK ca	se B-PL	JK (TO-	200AC)				
	8 -	0 =	eyelet t	erminals	gate a	ınd auxi	liary ca	thode u	nsoldere	ed leads)
		1 =	fast-on	terminal	s (gate	and aux	diliary ca	athode (unsoldei	red leads)
		2 =	eyelet t	erminals	(gate a	ınd auxi	liary ca	thode s	oldered	leads)
		3 = 1	fast-on t	erminals	(gate ar	nd auxilia	ary cath	ode solo	lered lea	ds)
	9 -	Crit	ical dV/	dt: • No	ne = 50	0 V/µs (standar	d selec	tion)	

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95076			

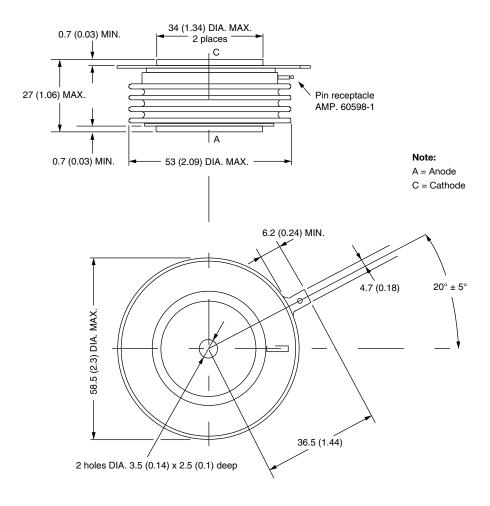
• L = 1000 V/µs (special selection)



B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)

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